CNA1011K (ON1113)

Photo Interrupter

For contactless SW and object detection

Overview

CNA1011K is a small size photocoupler package consisting of a high efficiency GaAs infrared light emitting diode used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element.

■ Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response: t_r , $t_f = 6.0 \mu s$ (typ.)
- Small output current variation against change in temperature

■ Absolute Maximum Ratings $T_a = 25$ °C

F	Symbol	Rating	Unit	
Input (Light emitting diode)	Power dissipation *1	P_{D}	75	mW
	Forward current	I_{F}	50	mA
	Reverse voltage	V _R	3	y.O
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	30	ojv .
	Emitter-collector voltage (Base open)	V _{ECO}	5,1110	V
	Collector current	I_{C}	20	mA
	Collector power dissipation *2	P _C	100	mW
Operating ambient temp	Topr	-25 to +85	°C	
Storage temperature	T _{stg}	-30 to +100	°C	

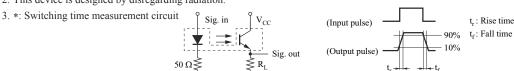
Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C

■ Electrical-Optical Characteristics T_a = 25°C±3°C

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
	Forward voltage	$V_{\rm F}$	$I_F = 50 \text{ mA}$		1.2	1.5	V
	Terminal capacitance	Ct	$V_R = 0 V, f = 1 MHz$		35		pF
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}$			200	nA
	Collector-emitter capacitance	C _C	$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}$		5		pF
Transfer characteristics	Collector current	I_{C}	$V_{CC} = 10 \text{ V}, I_F = 20 \text{ mA},$ $R_L = 100 \Omega$	0.3			mA
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.5	V
	Rise time *	t _r	$V_{CC} = 10 \text{ V}, I_C = 1 \text{ mA},$		6.0		μs
	Fall time *	t_{f}	$R_L = 100 \Omega$		6.0		μs

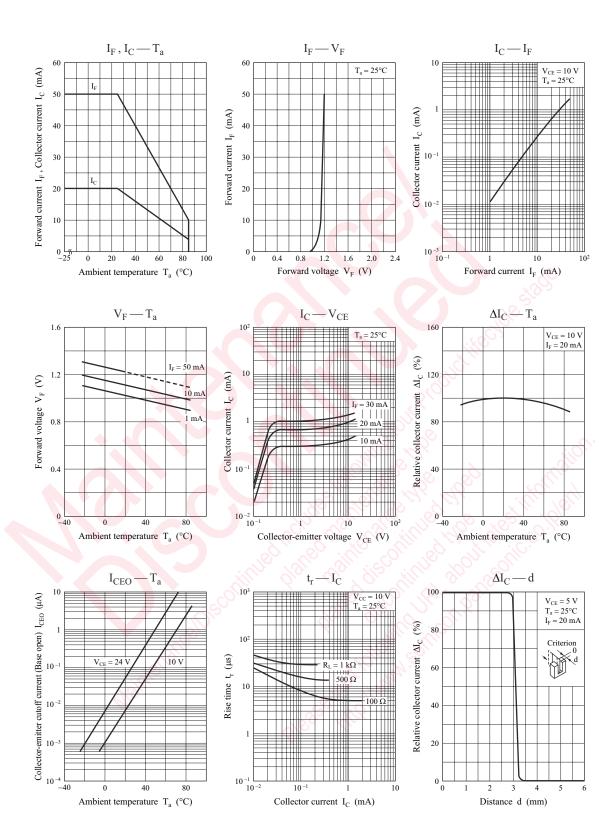
Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarding radiation.



Note) The part number in the parenthesis shows conventional part number.

^{*2:} Output power derating ratio is 1.34 mW/°C at $T_a \ge 25$ °C

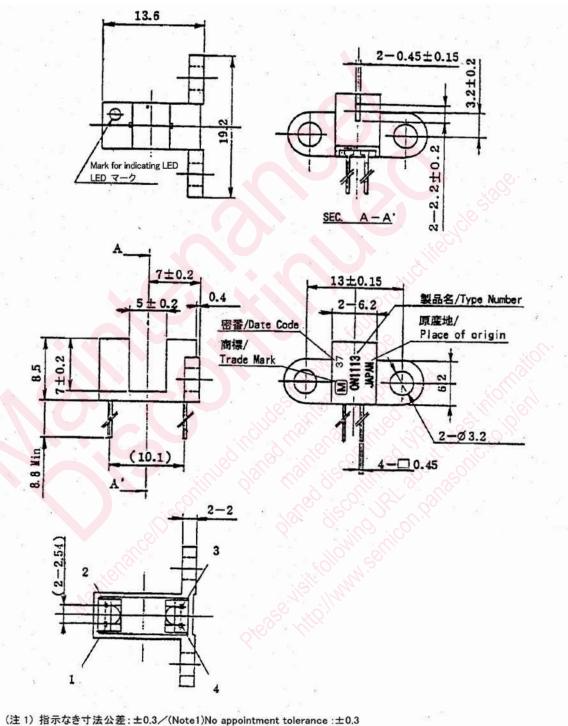


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Panasonic CNA1011K

■ Package (Unit: mm)

LSSSIR4S0004



- (注 2) マークは、目視又は顕微鏡に於いて解読できる事。

(Note2)What a mark sees an attention and can decode in a microscope.

- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Collector
 - 4: Emitter

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